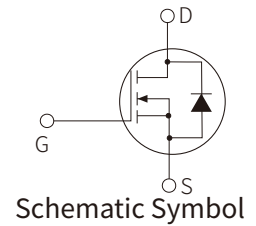
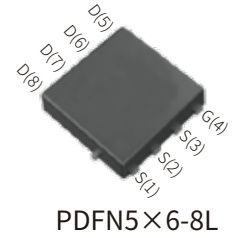


FEATURES

- | $R_{DS(ON)}$ Typ = 3.7m Ω @ V_{GS} = 10V
- | $R_{DS(ON)}$ Typ = 5.3m Ω @ V_{GS} = 4.5V
- | Advanced Split Gate Trench Technology
- | Excellent $R_{DS(ON)}$ and Low Gate Charge
- | 100% UIS TESTED!
- | 100% ΔV_{DS} TESTED!



APPLICATION

- | Load Switch
- | PWM Application
- | Power Management

APPROVALS

RoHS	Compliance with 2011/65/EU
HF	Compliance with IEC61249-2-21:2003

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	30	V
Pulsed Drain Current ⁽¹⁾	I_{DM}	320	A
Continuous Drain Current	I_D	80	A
		48	A
Power Dissipation $T_c = 25^\circ\text{C}$	P_D	52	W
Gate-to-Source Voltage	V_{GS}	± 20	V
Single Pulsed Avalanche Energy ⁽²⁾	E_{AS}	56	mJ
Junction & Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.4	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS (T_A=25°C)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =250μA	30			V
Gate Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nA
Drain Leakage Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			1.0	μA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _{DS} =250μA	1	1.5	2.2	V
Static Drain-Source ON-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A		3.7	4.8	mΩ
		V _{GS} =4.5V, I _D =15A		5.3	6.9	mΩ
Dynamic Characteristics						
Input capacitance	C _{iss}	V _{GS} =0V, V _{DS} =15V, f = 1MHz		953		pF
Output capacitance	C _{oss}			446		pF
Reverse transfer capacitance	C _{rss}			34		pF
Total Gate Charge	Q _g	V _{DS} =20V, V _{GS} =0 to 10V I _D =50A		17		nC
Gate-Source Charge	Q _{gs}			4.5		nC
Gate Drain("Miller") Charge	Q _{gd}			2		nC
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	V _{DD} =20V, V _{GS} =10V R _{GEN} = 3Ω, I _D =50A		6.5		nS
Turn-on Rise Time	t _r			2.7		nS
Turn-Off Delay Time	t _{d(off)}			26		nS
Turn-Off Fall Time	t _f			3.6		nS
Drain-Source Diode Characteristics and Max Ratings						
Drain to Source Diode Forward Voltage	V _{SD}	I _S =20A, V _{GS} =0V			1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F =50A di/dt = 100A/us		22		nS
Body Diode Reverse Recovery Charge	Q _{rr}			40		nC
Maximum Continuous Drain to Source Diode Forward Current	I _S				80	A
Maximum Pulsed Drain to Source Diode Forward Current	I _{SM}				320	A

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. E_{AS} condition: Starting T_J=25°C, V_{DD}=15V, V_G=10V, R_G=25ohm, L=0.5mH, I_{AS}=15A
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 0.5%

PARAMETER CHARACTERISTIC CURVE

Figure1: Power Capability

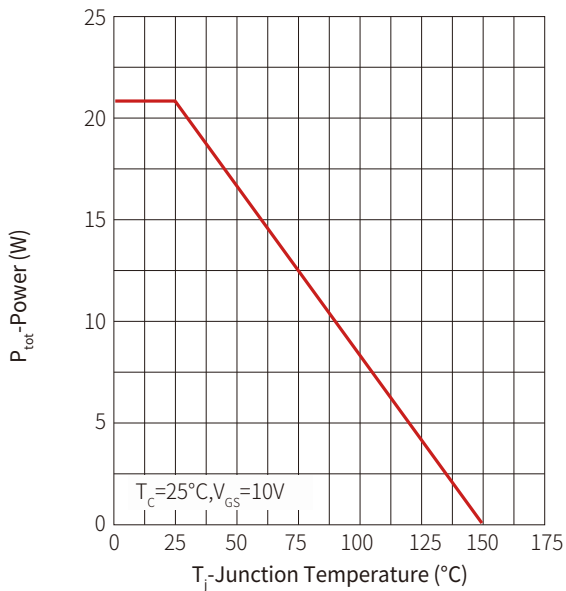


Figure2: Current Capability

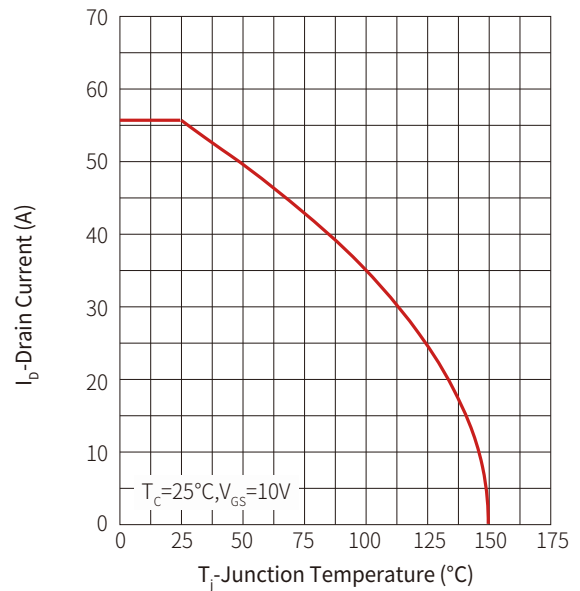


Figure3: Safe Operation Area

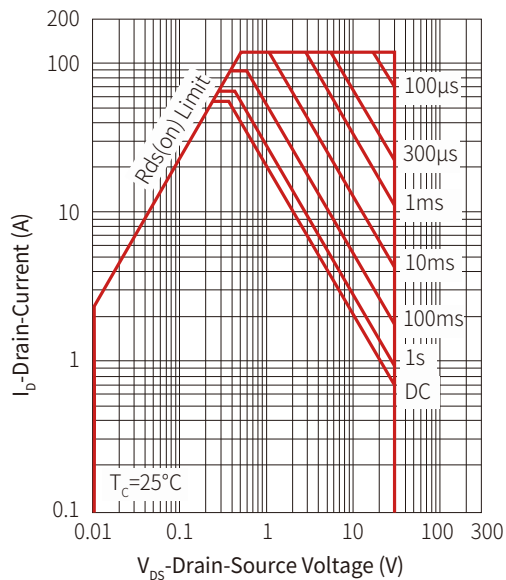


Figure 4: Transient Thermal Impedance

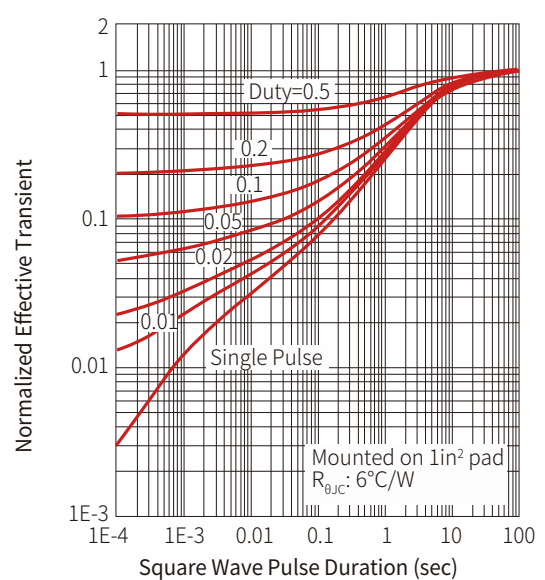


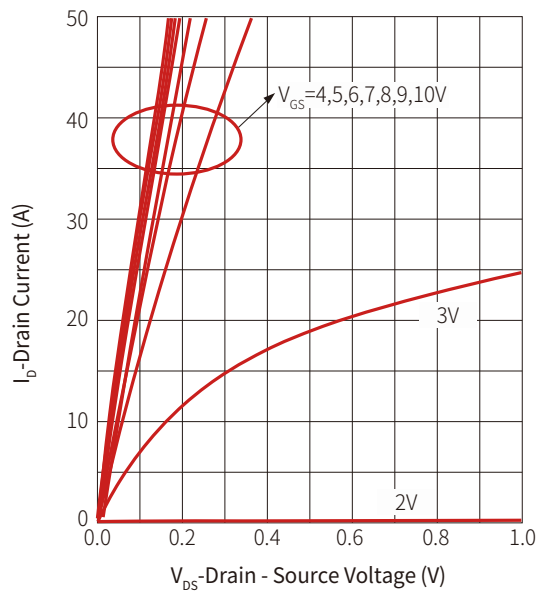
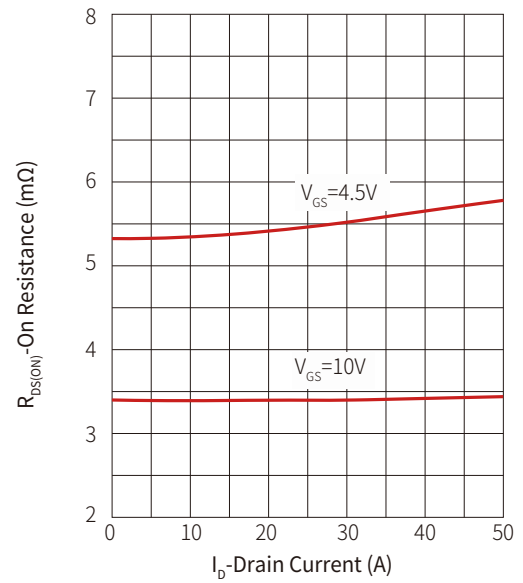
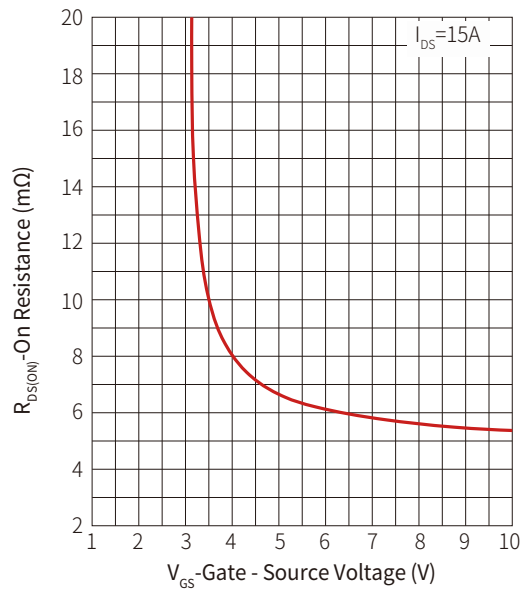
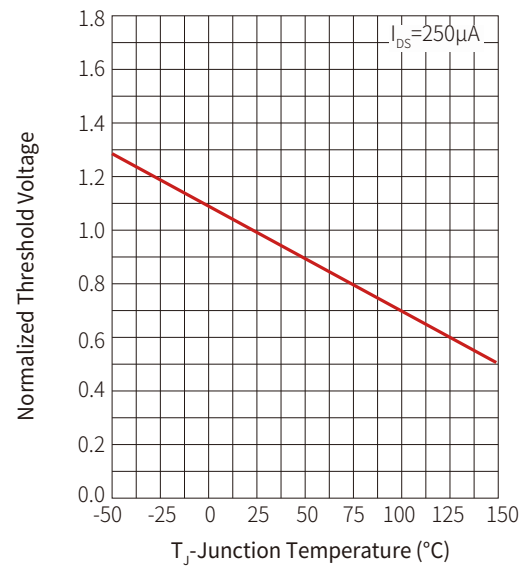
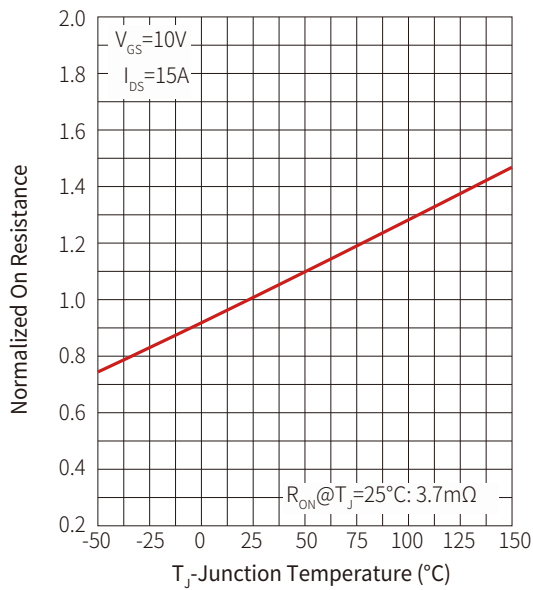
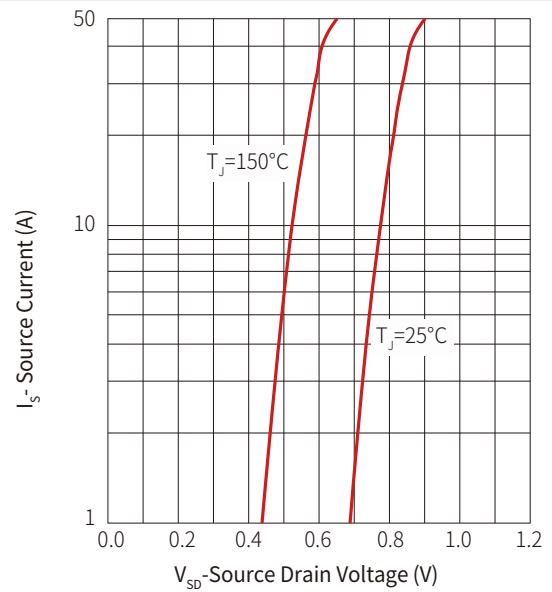
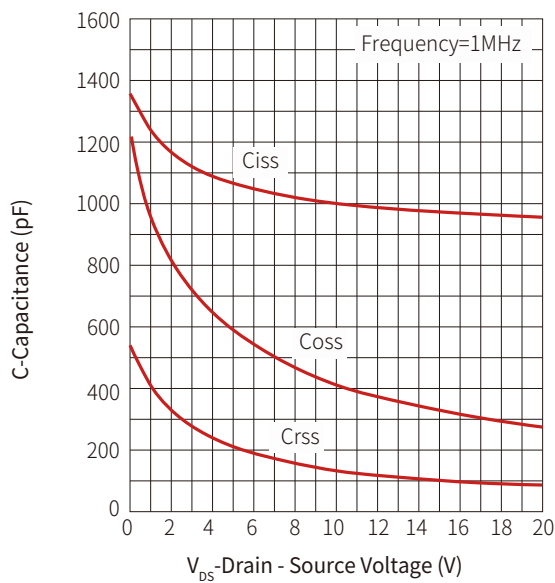
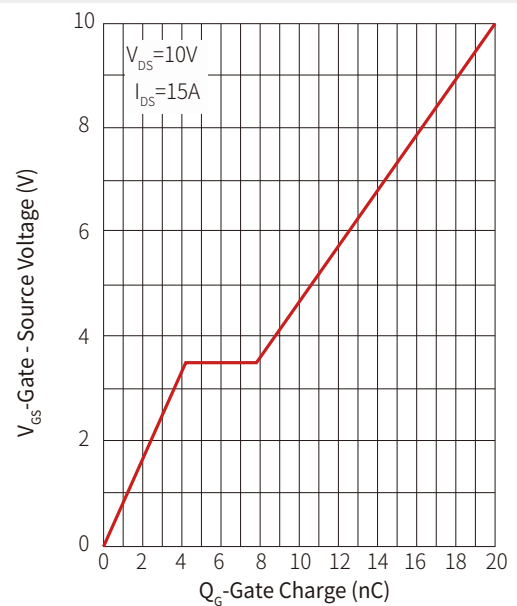
Figure 5: Output Characteristics

Figure 6: On Resistance

Figure 7: Transfer Characteristics

Figure 8: Normalized Threshold Voltage


Figure 9: Normalized On Resistance

Figure 10: Diode Forward Current

Figure 11: Capacitance

Figure 12: Gate Charge


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